

(19) World Intellectual Property  
Organization  
International Bureau



(43) International Publication Date  
27 January 2005 (27.01.2005)

PCT

(10) International Publication Number  
**WO 2005/008355 A1**

(51) International Patent Classification<sup>7</sup>: **G05F 1/56**

(74) Agent: **ITOH, Tadahiko**; 32nd Floor, Yebisu Garden Place Tower, 20-3, Ebisu 4-chome, Shibuya-ku, Tokyo 1506032 (JP).

(21) International Application Number:  
**PCT/JP2004/009694**

(22) International Filing Date: **1 July 2004 (01.07.2004)**

(25) Filing Language: **English**

(26) Publication Language: **English**

(30) Priority Data:  
**2003-191880** **4 July 2003 (04.07.2003)** **JP**

(71) Applicant (for all designated States except US): **RICOH COMPANY, LTD.** [JP/JP]; 3-6, Nakamagome 1-chome, Ohta-ku, Tokyo 1438555 (JP).

(72) Inventors; and

(75) Inventors/Applicants (for US only): **MORINO, Kohichi** [JP/JP]; 157-603, Idogayanakamachi, Minami-ku, Yokohama-shi, Kanagawa 2320052 (JP). **NEGORO, Takaaki** [JP/JP]; 1-5-202, Higashiteraohigashidai, Tsurumi-ku, Yokohama-shi, Kanagawa 2300018 (JP).

(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

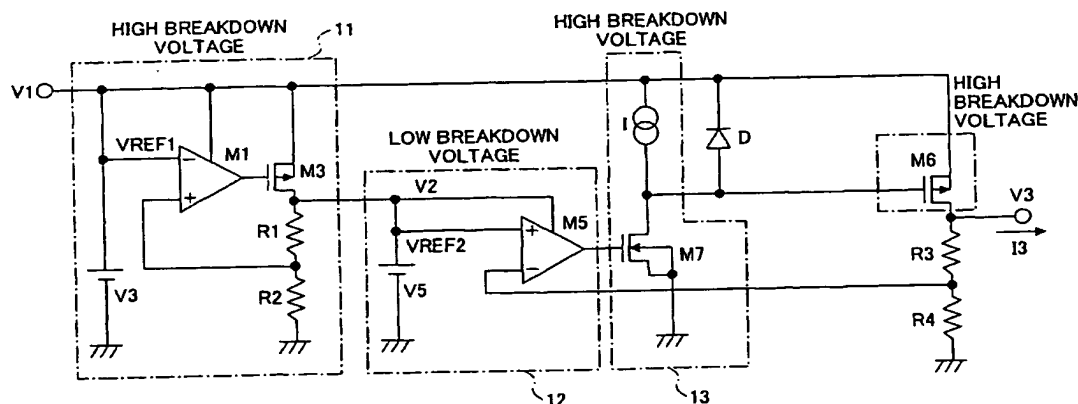
(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— with international search report

[Continued on next page]

(54) Title: **SEMICONDUCTOR DEVICE WITH HIGH-BREAKDOWN-VOLTAGE REGULATOR**



(57) Abstract: A semiconductor device comprises a high-breakdown-voltage regulator (11) configured to operate at a high input voltage (V1); a reference voltage generating circuit structured as a low-breakdown-voltage component and configured to receive an output voltage from the high-breakdown-voltage regulator to generate a reference voltage VREF2; a differential amplifier circuit (M5) structured as a low-breakdown-voltage component and configured to receive the output voltage from the high-breakdown-voltage regulator and the reference voltage from the reference voltage generating circuit to produce a drive voltage; an output driver (M6) structured as a high-breakdown-voltage component and configured to operate based on the drive voltage; and resistors (R3 and R4) connected in series to the output driver to divide an output voltage of the output driver and feed the divided voltage back to the differential amplifier circuit.



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*For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.*